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UNİSYS

DATE:

October 27, 1995

PPM-95-176

TO: FROM: S. Hull/311.1 K. Sabu/300.1

SUBJECT:

Radiation Report on HST/ADD

Part No. DAC8408A Control No. 10995A

ce: A. Sharma/311.0

R. Williams/300.1 OFA Library/300.1

A radiation evaluation was performed on DAC8408A (D/A Converter) to determine the total dose tolerance of these parts. A brief summary of the test results is provided below. For detailed information, refer to Tables I through IV and Figure 1.

The total dose testing was performed using a Co<sup>60</sup> gamma ray source. During the radiation testing, three parts were irradiated under bias (see Figure 1 for bias configuration), and two parts were used as control samples. The total dose radiation levels were 0.5, 1, 1.5, 2, 2.5, 3, 4, 5, 6 and 7 krads\*. The dose rate was between 0.029 and 0.058 krads/hour, depending on the total dose level, giving an effective average dose rate of approximately 0.01 krads/hour (see Table II for radiation schedule). After each radiation exposure parts were electrically tested according to the test conditions and the specification limits\*\* listed in Table III.

This radiation test is a continuation of that performed in PPM-95-151, dated May 18, 1995, using unitradiated samples from the same LDC. In that test, all irradiated parts exceeded specification limits for many test parameters after the 1 krad irradiation. The effective average dose rate in that test was approximately 0.07 krads/hour, which was seven times greater than in the present test. In this test, smaller increments of radiation dose were used, and the irradiated parts were annealed after each irradiation. This was done in an attempt to determine if the parts could tolerate somewhat more total dose radiation and show less degradation in Icc and other radiation-sensitive parameters at 2, 3, 4, 5, 6 and 7 krads, which are the levels of interest for the project.

All parts passed initial electrical measurements.

All parts passed all electrical tests throughout all irradiation steps up to and including the 1 krad irradiation level.

After the 1.5 krad irradiation, all irradiated parts exceeded the maximum specification limit of ±0.0010% nA for PSR\_B with readings ranging from 0.0014% to 0.0022%. In addition S/N 96 and 98 exceeded the maximum specification limit of ±0.0010% for PSR\_D with readings of 0.0011% and 0.0017%. After annealing for 24 hours at 25°C, all irradiated parts continued to exceed the maximum specification limit for PSR\_B with readings ranging from 0.0015% to 0.0022% and S/N 96 and 98 exceeded the maximum specification limit for PSR\_D with readings of 0.0011% and 0.0017%. After annealing second time for 24 hours at 25°C, same degradation continued.

\*The term rads, as used in this document, means rads(silicon). All radiation levels cited are cumulative.

<sup>\*\*</sup> These are manufacturer's pre-irradiation data specification limits. No post-irradiation limits were provided by the manufacturer at the time these tests were performed.

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After the 2 krad irradiation, all irradiated parts exceeded the maximum specification for PSR\_B and PSR\_D with readings ranging from 0.0014% to 0.0066% and 0.0051% to 0.0067%. In addition all irradiated parts exceeded the maximum specification limit of 50  $\mu$ A for ICC\_5V with readings ranging from 78  $\mu$ A to 122  $\mu$ A, and S/N 98 exceeded the maximum specification limit of  $\pm 0.0010\%$  for PSR\_A and PSR\_C with readings of 0.0014% and 0.0010%. After annealing for 72 hours at 25°C, all parts continued to degrade with the same parameters.

and ICC\_SV with readings ranging from 0.0020% to 0.0032%, 0.0126% to 0.0133%, 0.0110% to 0.0122% and 246  $\mu$ A and 323  $\mu$ A, and S/N 97 and 98 exceeded the maximum specification limit for PSR\_C with readings of 0.0011% and 0.0016%.

In addition, after the 2.5 Krad irradiation, all irradiated parts:

- exceeded the maximum specification limit of 50  $\mu A$  for ICC\_0V with readings ranging from 89  $\mu A$  to 123  $\mu A$
- exceeded the maximum specification limit of 50 μA for ICC\_0V with readings ranging from 89 μA to 123 μA
- exceeded the maximum specification limit of ±1 lsb for GFSE\_D with readings ranging from 1.03 lsb to 1.15 lsb
- readings for INL\_B are less than the minimum specification limit of -0.25 lsb with readings ranging from -0.332 lsb to -0.431 lsb
- readings for INL\_D are less than the minimum specification limit of -0.25 lsb with readings ranging from -0.353 lsb to -0.441 lsb.

In addition S/N 98 reading for INL\_A is less than the minimum specification limit of -0.25 lsb with reading of -0.287 lsb and the same part exceeded the maximum specification limit of -0.5 lsb for DNL\_B and DNL\_D with readings of 0.503 lsb and 0.525 lsb.

After 3, 4, 5, 6 and 7 Krad irradiation and annealing at least 24 hours at 25 °C, after every irradiation step, all parts continued to degrade in the above parameters.

Table IV provides a summary of the mean and standard deviation values for each parameter after different irradiation exposures and annealing step. A comparison of the degradation in the parts in this test vs. the previous testing shows that the parts exhibited less radiation-induced degradation; for example, in the previous test, all parts exceeded specification limits for lee after 1 krad, whereas, in this test, the parts did not exceed specification limits for lee until after 2.5 krads irradiation. In addition, there were no other failures at the 1 krad level, and the parts remained functional throughout the test up to 7 krads.

Any further details about this evaluation can be obtained upon request. If you have any questions, please call me at (301) 731-8954.

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### CAREPORTS\284.DOC

## TABLE 1. Part Information

Generic Part Number:

HST/ADD

Part Number:

5962-8967801XA

HST/ADD

Control Number:

10995A

DAC8408A

Charge Number:

EE61735

Manufacturer:

Analog Devices Inc.

Lot Date Code:

9449

Quantity Tested:

5

Serial Number of

Control Samples:

80, 81

Serial Numbers of

Radiation Samples:

96, 97, 98

Part Function:

D/A Converter

Part Technology:

CMOS

Package Style:

28-pin DIP

Test Equipment:

A540

Test Engineer:

C. Nguyen

<sup>\*</sup> No radiation tolerance/hardness was guaranteed by the manufacturer for this part.

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## TABLE II. Radiation Schedule for DAC8408A

EVENTS	TABLE II. Radiation Schedule for DAC 6408A	DATE
1) INITIAL ELECTRICAL MEAS	SUREMENTS	07/05/95
2) 0.5 KRAD IRRADIATION (0.0	029 KRADS/HOUR)	07/05/95
POST-0.5 KRAD ELECTRICAL	MEASUREMENT	07/06/95
3) I KRAD IRRADIATION (0.02	9 KRADS/HOUR)	07/06/95
POST-1 KRAD ELECTRICAL M	IEASUREMENT	07/07/95
4) 72-HOUR ANNEALING @25°	°C	07/07/95
POST-72 HOUR ANNEAL ELEC	CTRICAL MEASUREMENT	07/10/95
5) 1.5 KRAD IRRADIATION (0.0	029 KRADS/HOUR)	07/10/95
POST-1.5 KRAD ELECTRICAL)	MEASUREMENT	07/11/95
6) 24-HOUR ANNEALING @25° POST-24 HOUR ANNEAL ELEC	CTRICAL MEASUREMENT	07/11/95 07/12/95
7) 24-HOUR ANNEALING @25°	CC	07/12/95
POST-24 HOUR ANNEAL ELEC	CTRICAL MEASUREMENT	07/13/95
8) 2 KRAD IRRADIATION (0.02	9 KRADS/HOUR)	07/13/95
POST-2 KRAD ELECTRICAL M	MEASUREMENT	07/14/95
9) 72-HOUR ANNEALING @25°	C	07/14/95
POST-72 HOUR ANNEAL FLEC	TRICAL MEASUREMENT	07/17/95
10) 2.5 KRAD TRRADIATION (0.	.029 KRADS/HOUR)	07/18/95
POST-2.5 KRAD ELECTRICAL I	MEASUREMENT	07/19/95
11) 24-HOUR ANNEALING @25	5°C	07/20/95
POST-24 HOUR ANNEAL ELEC	TRICAL MEASUREMENT	07/21/95
12) 3 KRAD IRRADIATION (0.00 POST-3 KRAD ELECTRICAL MI	29 KRADS/HOUR) EASUREMENT	07/25/95 07/26/95
13) 24-HOUR ANNEALING @25	5°C	07/26/95
POST-24 HOUR ANNEAL ELEC	TRICAL MEASUREMENT	07/27/95
14) 72-HOUR ANNEALING @25	5°C	07/27/95
POST-72 HOUR ANNEAL ELEC	TRICAL MEASUREMENT	08/01/95
15) 4 KRAD IRRADIATION (0.05)	58 KRADS/HOUR)	08/01/95
POST-4 KRAD ELECTRICAL MI	EASUREMENT	08/02/95
16) 5 KRAD IRRADIATION (0.05	58 KRADS/HOUR)	08/02/95
POST-5 KRAD ELECTRICAL MI	EASUREMENT ,	08/03/95
17) 6 KRAD IRRADIATION (0.05	58 KRADS/HOUR)	08/03/95
POST-6 KRAD ELECTRICAL MI	EASUREMENT	08/04/95
18) 72-HOUR ANNEALING @25	°C.	08/05/95
POST-72 HOUR ANNEAL ELEC	TRICAL MEASUREMENT	08/07/95
19) 7 KRAD IRRADIATION (0.05	58 KRADS/HOUR)	08/07/95
POST-7 KRAD ELECTRICAL ME	EASUREMENT	08/08/95

PARTS WERE IRRADIATED AND ANNEALED UNDER BIAS, SEE FIGURE 1.

 $Total\ irradiation\ time = 34\ days = 816\ hours,\ Total\ radiation\ dose = 7\ krads;\ Average\ dose\ rate = 0.0086\ krads/hour$ 

Table III. Electrical Characteristics of DAC8408A

			· · · · · · · · · · · · · · · · · · ·	
Test#	Test Name	Min	Max	Condition
I	lcc_0v		50.00 μΑ	Vin = 0.0 V
2	Icc_5V		50.00 μΛ	Vm = 5.0 V
3	lcc_vil		1.00 mA	Vin = 0.8 V
4	Icc_vih		Azn 00.1	Vin = 2.4 V
5	Jih DB7	-1.00 µA	1.00 μΑ	Viest ~ 5.0 V
6	lih DB6	-1.00 μA	1.00 µA	V test = 5.0 V
-7	lih DB5	-1.00 μA .	1.00 μΑ	Vicst = 5.0 V
R	lih DB4	-t.00 μΛ	1.00 μΑ	$V \cos t = 5.0 V$
9	1ih-DB3	-t.00 μA	1.00 µA	$V_{test} = 5.0 V$
10	1ih DB2	-1.00 μA	1.00 µA	Vtest = 5.0 V
11	lih DBT	-1.00 μA	1.00 μΑ	Vicst = 5.0 V
12	Jih DB0	-1.00 μΛ	1.00 µA	$V_{test} = 5.0 \text{ V}$
13	lih DS1	-t.00 μA	1.00 μA	V test = 5.0 V
14	lih DS2	-1.00 μA	1.00 µA	$V_{test} = 5.0 \text{ V}$
15	lib AB_	-1.00 μA	1.00 μΛ	Vicst = 5.0 V
16	lih RW	-1.00 μΛ	1.00 µA	Viest - 5.0 V
17	lil DB7	-1.00 μA	1.00 µA	V test = 0.0 V
18	til DB6	-£.00 µA.	1.00 μΑ	Vtest = 0.0 V
19	HI DB5	-1.00 μA	1.00 μΛ	Vtcst = 0.0 V
20	lii DB4	-1.00 µЛ	1,00 μΑ	Vtest = 0.0 V
21	Iil DB3	-L,00 µA	1.00 µA	Vtest = 0.0 V
22	lit DB2	-l.00 μA	1.00 μA	Vtest = 0.0  V
23	li) DBI	-1.00 μA	1.00 μA	V(cst = 0.0  V)
74	III DB0	-L.00 AT	1.00 µA	Vtest = 0.0  V
25	Iil DS1	-L.00 µA	1.00 μΑ	
26	Iii DS2	-1.00 µA	1.00 μΑ	$V_{test} = 0.0 \text{ V}$ $V_{test} = 0.0 \text{ M}$
27	fil AB_	-1.00 μA	1.00 µA	Vtest = 0.0 V $Vtest = 0.0 V$
28	Ia RW_	-1.00 μΑ		Vtest = 0.0  V
29	Voh DB7	4.00 V	1.00 pA	V(est = 0.0  V)
30	Voh DB6	4.00 V		lout = 0.4 mA
31	Voh DB5	4.00 V		lout = 0,4 mA
32	Voli DB4	4.00 V		lost = 0.4  mA
33	Voh DB3	4.00 V		lout = 0.4 mA
34	Yoh DB3	4.00 V		lout = 0.4 mA
35	Voh DB1	4.00 V		lout = 0.4  mA
36	Voli DB0			lout = 0.4 mA
37	Vol DB7	4.00 V	0.400.33	lout = 0.4 mA
38	Vol DB6		0.400 V	lout = 1.6 mA
39	Vol DB5		0.400 V	lout = 1.6  mA
40			0.400 V	lout = 1.6 mA
41	Vol DB4		0.400 V	lout = 1.6 mA
42	Vol DB3		0.400 V	fout = 1.6 mA
42 43	Vol DB2		0.400 V	lout = 1.6  mA
_	Vol DB1		0.400 V	$\cdot \text{ fout} = 1.6 \text{ mA}$
44	Vol DB0		0.400 V	lout = 1.6 mA
45	GSFE_A	-1.00 Isb	1.00 lsb	Gain error DAC A
46	GFSE B	-1.00 lsb	1.00 fsb	<ul> <li>Gain error DAC B</li> </ul>
47	GFSE_C	-1.00 lsh	1.00 tsb	Gain error DAC C
48	GFSE_D	-1.00 lsb	1.00 isb	Gain error DAC D
49	PSR_A	-0.0010 %	0.0010 %	Delta VDD +/-10%
50	PSR_B	·0.0010 <b>%</b>	0.0010 %	Delta VDD = +/-10%
51	PSR_C	-0.0010 %	0.0010 %	Delta VDD = +/-10%
52	PSR_D	-0.0010 %	0.0010 %	Ocita VDD = +/-10%
5.3	INL_A	-0.250 lsb	0.250 lsb	
54	DNL_A	-0.500 lsb	0.500 fsb	
55	INL_B	-0.250 lsb	0,250 156	
56	DNL_B	-0.500 lsb	0.500 lsb	
57	INU_C	-0.250 lsb	0.250 lsb	
58	DNL_C	-0.500 Isb	0.500 1s6	
59	INL_D	-0.250 lsb	0.250 կչն	
60	DNL_D	🐔 -0 500 Isb	0.500 lsb	

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## TABLE IV: Summary of Electrical Measurements after Total Dose Exposures and Annealing for DAC8408A /1

							Total Dose Exposure (krads)						Annealing Rad level				Annealing		Rad level	
					Ini	6al	0.3	5	1		1	5	241	hrs	1 2	<u> </u>	72	113	2.	5
Test			Spec. I	.im./2									@:	25°C				5°C	-	_
#	Parameters/3	Units	min	max	mean	ed	mean	ad	mean	sd	mean	sd	DICAM	sd	пеяц	sd	mean	3d	теал	٤d
1	Icc_0v	uА		50	0	0	0	0	10	0	0.00		2	2	32	1 10	31	10	106	19
2	Icc_5V	υA	· -	50	0	0	0	0	2	2	8	3	13	5	96	23	95	23	284	38
3	Icc_vil	mA		1	0	0	0	0	0	0	0	0	0	0	0	0	0		<u> </u>	-0
4	lee_vili	mΑ	J •	<u> </u>	0.45	0.01	0.42	0.01	(L40	0.01	0.39	0.01	0.40	0.01	0.46	0.03	0.46	0.02	0.64	0.04
5	lih DB	uA	-1	1	-0.21	0.01	-0.2	0.04	-0.2	0.03	-0.2	0.01	~0.19	0.03	-0.2	0.03	-0.2	0	-0.2	0.04
- 6	lih DS	u.A	-1	1	-0.32	0.07	-0.4	0.04	-0.4	0.01	-0.4	0.01	-0.3	0.07	-0.3	0.02	-0.4	0.05	-0.4	n
7	IIA AB	цA	-1	ı	÷0.2	0.08	-0.2	0.02	-0,22	0.03	-0,3	0.04	-0.3	0.02	-0.3	0.02	-0.3	0.02	-0.3	2.07
8	Iih RW_	uA	-1	1	-0.4	0.01	-0.3	0.08	-0.4	0.02	-0.3	0,09	-0.4	0.04	-0.3	0.15	-0.37	0.06	-0.4	0.08
9	GI DB	qΛ	<b>-</b> I	1	-0.18	0,01	0.2	0.05	-0.1	0.03	-0.2	0.03	-0.2	0.01	-0.2	0.02	-0.2	0	-0.2	0
10	E1 DS	τA	-1	1	-0.2	0.03	-0.2	0.01	-0.2	0.05	-0.2	0.05	-0.2	0.02	-0.25	0.04	-02	0.01	-0.2	0.03
11	LLI AR_	цÁ	-1	1	-0.2	0.03	-0.2	0,04	-0.2	0.02	-0.2	0.01	0.1	0	4119	0,04	-0.2	0.03	-0.2	0.02
12	fil RW_	uA	-1	1	H0.2	0.02	-0.19	0.06	-0.2	0.02	-0.2	0.03	-0,37	0.01	-0.2	0.06	-0.2	0.01	-0.2	0.04
13	Voh DB	Y	4		4.29	0.01	4.25	0.09	4.29	0.02	4.29	0	4.28	0	4.29	0.	4.29	0	4.25	0.02
14	Vol DB	v	-	4	0.09	0	0.09	0	0.10	0.01	0.10	0.01	0.09	0	4.29	0	0.09	0.01	0.10	0.03
15	GFSE_A	lsb	-1	1	-0.54	0.09	0.54	0.12	-0.5]	0.11	-0.52	0.09	0.32	0.09	0.49	0.11	-0.48	0.12	-0.47	0.22
16	GFSE_B	lsb	-1		-0.61	0.18	-0,60	0.19	-0.58	0.18	-0.42	0.16	0.42	0.16	0,19	0.14	0.20	0.13	0.83	0.35
1.7	GFSE_C	lsb	-1	1	0.43	0.07	-0.44	0.09	-0.37	0.06	-0,42	0.11	0,44	0.12	-0.39	D.16	-0.41	0.16	-0.35	0.18
. 19	GFSE_D	lsb	ı.	1	-0.51	0.13	-0.49	0.13	-0.21	0.52	-0.33	0,05	+0.39	0.14	0.26	9.08	0.28	0.01	1,09	0,06
19	PSR_A	%	-0.0010	0.0010	.0002	4E-4	.0005	4E-4	.0007	8E-5	.0005	6E-5	.0005	7E-5	,0009	4E-4	.0008	4E-4	.0026	6E-4
20	PSR_B	%	-0.000	0.0010	.00002	3E-5	.00009	5E-5	.0004	5E-5	:.0017	4E-4	.0017	4E-4	.0067	7E-4	.0067	8E-4	0.013	4E-4
21_	PSR_C	%	-0.0010	0.0010	- 00003	4E-5	+ 00002	9E-6	.00007	E-4	.00004	2E-4	.00005	5TC-\$	0004	5E-4	::0003	3E-4	.0011	4E-4
22	PSR_D	%	-0.0010	0.0010	0004	6E-5	6003	5E-5	000038	4E-4	.0012	4 <b>E-4</b>	.0012	4E-4	.0059	8E-4	.0059	9B-4	.0116	6E-4
	INL_A	lsb	-0.25	0.25	0	0.03	, D	0.04	-0.04	0	-0.04	10.0	-0.04	0 :	-0,07	0.05	-0.07	0.05	-0.09	0.20
24	DNL_A	!sb	-5	5	0.04	U	D.04	0,01	0:04	-0	0.05	0.01	0.05	D.O1	0.09	0,06	0.09	0.06	0.18	0.11
25	INL_B	lab	-0.25	0.25	0:004	0.04	0.03	0.01	0.04	0.01	-0.06	0.01	-0.06	0	-0,21	0.01	.0.2t	0.01	-0.38	0.05
-	DNL_B	lsb	-5	5	0.04	O	0.04	Đ	0.06	g	0.09	0.01	0.09	0.01	0.26	0,01	0.27	0.02	0.46	0.05
	INL_C	lsb	-0.25	0.25	0.03	0.01	0.03	0.01	0.01	0.03	0.05	0.16	-0.04	0.01	-0.06	0,04	-0.06	0.04	-0.12	0.07
-	DNL_C	ls b	-5	5	0.04	0	0.04	a	0.04	0.01	0.13	0.11	0.05	0.02	6.09	80.0	0,09	0.07	0.19	0.13
$\rightarrow$	INID	lsb	-0.25	0.25	0.003	0.05	0.01	0.05	0.02	0.06	-0.03	0.07	+0.07	10.0	-0.21	0.04	-0.2	0.04	-1.39	0,04
30	DNT_D	lsp.	-5	_ 5	0.05	0.02	0.05	0.01	0.07	0.01	0.10	0.02	0.11	0.02	(£25	0.04	0.25	0.04	0.47	0.05

## Notes:

- 1/ The mean and standard deviation values were calculated over the three parts irradiated in this testing. The control samples remained constant throughout the testing and are not included in this table.
- 2/. These are manufacturer's pre-irradiation data sheet specification limits. No post-irradiation limits were provided by the manufacturer at the time the tests were performed.
- 3/ In this table, some test parameters have been combined for clarity. Complete results for all test parameters are available on request.

Radiation-sensitive parameters: Icc, Voh, GFSE, PSR, INL and DNL.

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# TABLE IV: Summary of Electrical Measurements after Total Dose Exposures and Annealing for DAC8408A /1

					Алреац	ing	Rad Level		Annealing		Rad Level		Rad Level		Rad Level		Annealing		Rad Level	
					24	hrs	J		72	hrs	4		. 5		6				7.20	1,6761
Test		Spec. Lim/2		@25°C				@25°C		i			j				72 hrs @25°C			
#	Parameters/3	Units	an in	132 AX	or Cau	sd	mean	8d	iznean	ad	mean	sd	mean	sď	mesn	1	, –			
1	lec_0V	цA	<del>,</del>	50	108	19	252	27	239	25	440	41	727	93	970	9d 1 44	mean 978	8d 43	mean	sd
2	fc¢_5V	ШÁ	<u> </u>	50	290	]41	592	57	578	55	1014	94	1584	145	2241	115	2255	119	1273	89
3	Icc_vil	mð		1	0	D	0.04	0	0.03	0	0.06	0.01	0.14	0.09	0.06	0.11	0.07	0.11	2965 0.03	217
. 4	Icc_vih	ВĀ	r <u>i</u> -	1	0.64	0.04	0.93	0.06	0.92	0.06	1.33	0.09	1.58	0.15	2.51	0.11	2:53	0.11	3.21	0.04
<u> </u>	lih DR	υA	· -i	1	-0.2	0.01	-0.2	0.01	-0.2	0.01	-0.2	0.02	-0.2	0.02	-0.2	0.07	-0.2	0.01	*******	0.21
5	lik DS	ūΛ	.; -1	1	-0.4	0.07	-0.4	0.06	-0.4	0.04	-0.4	0.11	-0.4	0.06	-0.04	0.07	0.4	0.01	-0.2	0.01
7	Jih AB	uA	-1	1	-0.2	0,07	-0.3	0.02	0.3	0.05	-0.3	0.04	0.3	0.05	-0.3	0.09	-0.3	0.04	-0.4 -0.2	0.02
3	lih RW_	υA	-1	1	×0,3	0.02	+0.4	0.03	+0.3	0.08	+0.2	0.10	-0.3	0.09	-0.1	0.05	-0.3	0.04	+0.3	0.02
. 9	Jii DB	uÁ	-1	1	* <b>0.1</b>	0.02	-0.1	0.06	-021	0.06	-0.2	0.02	-0.2	0.01	-0.2	0.04	-0.2	0.08	-0.18	0.02
10	Iii ds	uA	-I	1		0.06	-0.2	0	0,19	0.02	-0.3	0.03	-0.2	0.01	-0.2	0.04	-0.2	0.04	-0.2	0.05
11	Iil AB_	οA	<u>-1</u>	1	-0.1	0.02	0.2	0.04	+0.2	0,04	-0.7	0.01	0.3	0	-0.2	0	0.2	0.02	-0.1	0.03
[2	GI RW_	nA.	-1	1	-0.2	0.04	+0.2	0	-0.2	0.02	-0.2	0.09	0.2	0.03	-0.25	0.05	-0.2	0.03	+0.2	0.03
13	Voh DB	Y	<del></del>	-	4.26	0	4.22	0	4.29	0.01	4.16	0,02	4.08	0.02	3.96	0.03	3.95	0.03	3.8)	0.04
14	Vel DB	Y	<u>'</u>	4	0.09	0	0.09	0.07	0.09	0.01	0.09	0	0.09	0	0.10	0	0.10	0	6.10	0
15	GFSE_A	hb		l l	-0.43	0.19	9.05	0.29	0.07	0.28	0.85	0.39	1.65	0.50	120	116	120	115	204	68
16	GFSE_B	BP.		1	1.07	0.15	1,89	0.17	1.85	0.13	2.84	0.16	3.83	0,29	5.13	0.32	5.16	0.31	5.39	0.32
17	GFSE_C	lsb.	1	1	-0.34	0.17	0.15	0.16	0.15	0.17	0.99	0.14	1.82	0.16	126	123	126	123	167	70.9
18	GFSE_D	lsb		1	1.14	0.03	1,97	0.05	1.29	0.10	2.91	0.07	3,95	0.12	5.22	0.21	5.11	0.21	6,42	0.24
19	PSR_A	%	-0.0010		.0015	1.1E-J	.0032	1.8E-3	.0035	1.9E-3	.0058	3.4E-3	.0085	5 <b>E</b> -3	.0123	8.1E-3	.0121	8E-3	.0156	1.1E-2
20	PSR_B	%	-0.0010	0.0010	.0134	6 <b>E</b> -4	.02	8E-5	.0196	1.5E-3	0279	1E-3	.0361	2.6E-3	0501	2.7E-3	.0502	3E-3	0632	4.1E-3
21	PSR_C	%	-0.0010	D.0010	.0009	7E-4	.0029	3E-4	.0031	3£-4	.0059	1.7E-3	0091	3,3E-3	.0138	5.4E-3	.0137	6E-3	0185	7.5E-3
	PSR_D	%	-0.0010	0.0010	0121	8E-4	.0183	1E-3	.0179	1.6E-3	.0255	1.2E-3	.0330	2.7E-3	D459	2.8E-3	016	3.1E-3	0582	4.3E-3
_	INL_A	lsb	-0.25	0.25	-0.65	0.13	-0.23	0.03	-0.23	0.08	+0,43	0.11	-0.65	0.15	16.7	31.7	16.2	29.6	-378	294
	DNI_A	del		5	0.17	0.13	0.32	0.16	0.32	0.17	0.54	0.18	0.77	0.24	31.7	51.9	32.2	54,1	358	308
-	INL_B	طفا		0.25	-0.42	0.02	-0.62	D.OL	-1.40	0.67	0.85	0.01	-L06	0.03	-1.34	0.03	-1.34	0.03	-2.08	0.84
$\overline{}$	DNL_B	lsb		5	0.47	0.01	0,68	0.02	1.12	0.37	0.94	0.02	1.18	0.05	L47	0.06	1,46	0.03	1.95	0.34
	INL_C	lsb	-0.25	0.25	-0.12	0.07	-0.16	0.35	0.29	0.12	-0.48	0.12	-0.75	0.12	-56.9	96.9	58.5	99.9	-160	95.6
-	DNL_C	lsb	-5	5	0.19	0.13	0.36	0.14	0.33	0.15	0.35	0.15	0.76	0.12	\$7.1	88.5	663	[13	208	53.7
$\longrightarrow$	INL_D	isb	-0.25	0.25	0.41	0.03	<b>-0.60</b>	0.04	-0.59	0.04	-0.83	0.05	1.05	0.07	-1,33	0.07	.:F1:34	0.07	-1.59	0.07
30	DNL_D	lsh	-5	5	0.48	0.03	0.68	0.04	9,66	0.03	0,91	0.05	1.20	0.07	1,48	0.07	1.46	0.07	1.77	0.08

## Notes:

- 1/ The mean and standard deviation values were calculated over the three parts irradiated in this testing. The control samples remained constant throughout the testing and are not included in this table.
- 2/ These are manufacturer's pre-irradiation data sheet specification limits. No post-irradiation limits were provided by the manufacturer at the time the tests were performed.
- 3/ In this table, some test parameters have been combined for clarity. Complete results for all test parameters are available on request.

Radiation-sensitive parameters: Icc, Voh, GFSE, PSR, INL and DNL.

Figure 1. Radiation Bias Circuit for DAC8408A

